

1000V N-Channel MOSFET

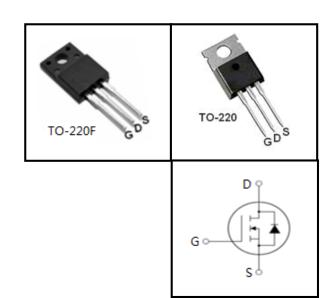
FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	Device Package			
CS5N100HF	TO-220F	CS5N100HF		
CS5N100HP	TO-220	CS5N100HP		



Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted					
Parameter	Symbol -	Val	l lmit		
Parameter		TO-220F	TO-220	Unit	
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	1000		V	
Continuous Drain Current	I _D	5		А	
Pulsed Drain Current (note1)	I _{DM}	20		А	
Gate-Source Voltage	V _{GSS}	±30		V	
Single Pulse Avalanche Energy (note2)	E _{AS}	180		mJ	
Avalanche Current (note1)	I _{AS}	6		Α	
Repetitive Avalanche Energy (note1)	E _{AR}	108		mJ	
Power Dissipation (T _C = 25°C)	P _D	25	70	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C	

Thermal Resistance				
Parameter	Symbol	Va	1114	
		TO-220F	TO-220	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	5	1.78	12/\\
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60	K/W



CS5N100HF, CS5N100HP

Specifications $T_J = 25^{\circ}C$, unless otherwise noted								
Parameter	Symbol	Test Conditions	Value			Unit		
	- Cynnoon	root contained	Min.	Тур.	Max.			
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_{D} = 250\mu A$	1000			V		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 1000V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA		
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 30V$			±100	nA		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		4.0	V		
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_D = 2.5A$		1.6	2	Ω		
Dynamic								
Input Capacitance	C _{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0MHz$		1502		pF		
Output Capacitance	C _{oss}			139				
Reverse Transfer Capacitance	C _{rss}			30				
Total Gate Charge	Q_g	$V_{DD} = 800V, I_{D} = 5A,$ $V_{GS} = 10V$		56		nC		
Gate-Source Charge	Q_{gs}			6				
Gate-Drain Charge	Q_{gd}	65		25				
Turn-on Delay Time	t _{d(on)}			46		ns		
Turn-on Rise Time	t _r	$V_{DD} = 500V, I_{D} = 5A,$		24				
Turn-off Delay Time	t _{d(off)}	$R_G = 25 \Omega$		290				
Turn-off Fall Time	t _f			53				
Drain-Source Body Diode Character	istics							
Continuous Body Diode Current	I _S	T			5	Α		
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			20			
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C$, $I_{SD} = 2.5A$, $V_{GS} = 0V$			1.4	V		
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V, I_{S} = 5A,$		479		ns		
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /μs		1.3		μC		

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}C$
- 3. Pulse Test: Pulse width ≤ 300µs, Duty Cycle ≤ 1%



Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^{\circ}C$)

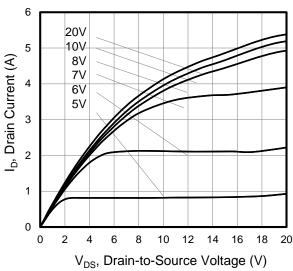


Figure 2. Body Diode Forward Voltage

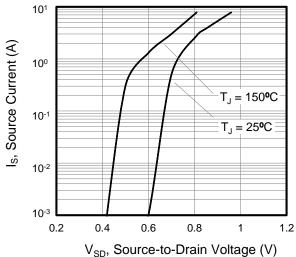


Figure 3. Drain Current vs. Temperature

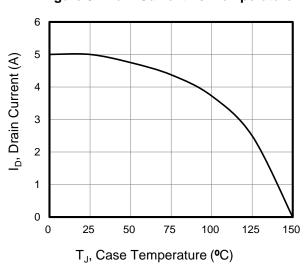


Figure 4. BV_{DSS} Variation vs. Temperature

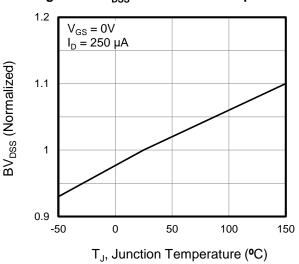


Figure 5. Transfer Characteristics

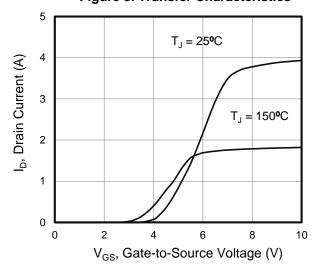
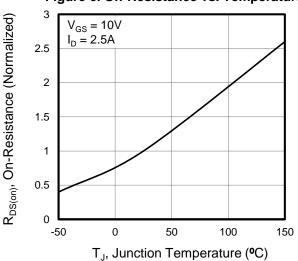


Figure 6. On-Resistance vs. Temperature



CS5N100HF, CS5N100HP

Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

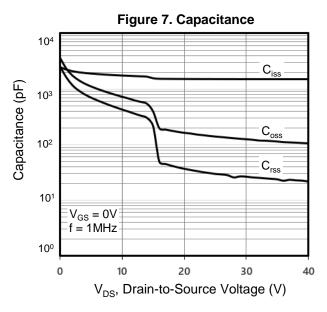
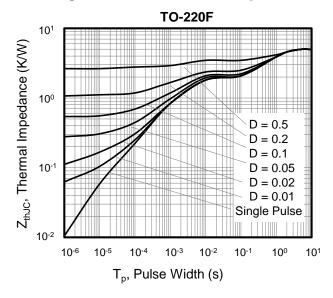


Figure 9. Transient Thermal Impedance



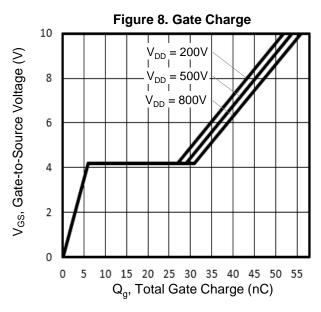


Figure 10. Transient Thermal Impedance

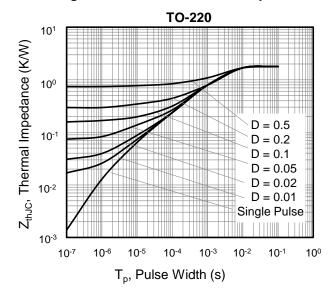




Figure A: Gate Charge Test Circuit and Waveform

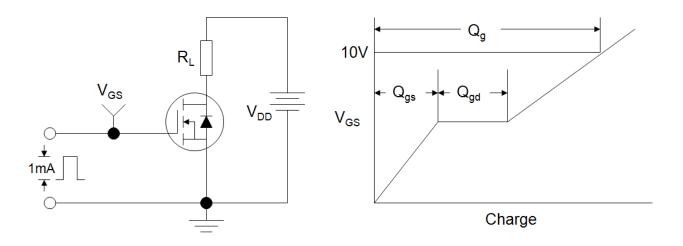


Figure B: Resistive Switching Test Circuit and Waveform

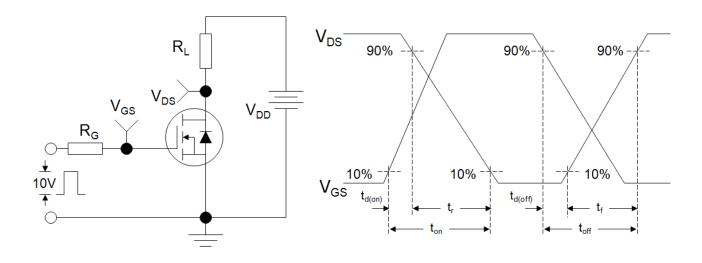
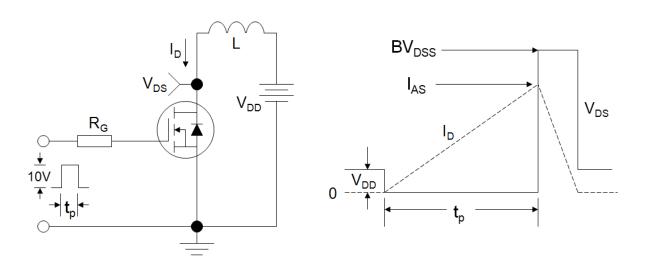
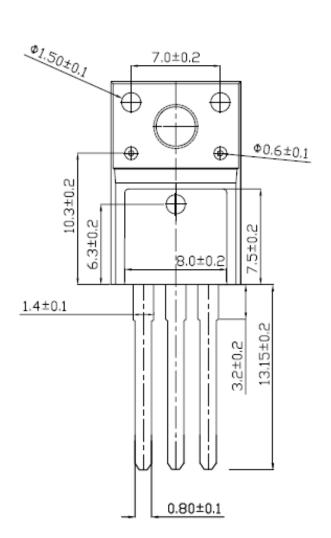


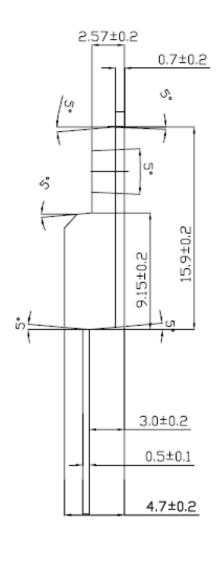
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





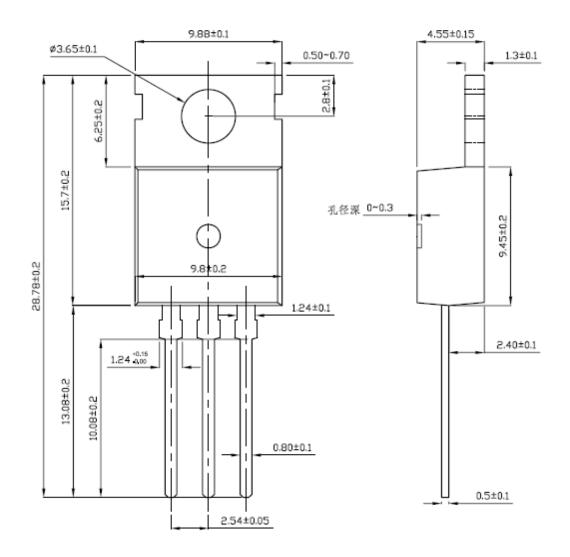
TO-220F







TO-220



CS5N100HF, CS5N100HP

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